



PerF≝T[™]Power Transistor

FEATURES

- Excellent FOM
- Reliability meets AEC-Q101 requirements
- Wettable flank leads for enhanced AOI
- 100% UIS and Rg tested
- 175°C operating junction temperature
- RoHS Compliant
- Halogen-free

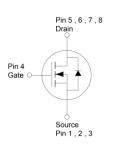
KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
V _{DS}		100	V	
	V _{GS} = 10V	10	0	
R _{DS(on)} (max)	$V_{GS} = 7V$	12	mΩ	
Qg	$V_{GS} = 10V$	20	nC	



APPLICATIONS

- Solenoid and motor drivers
- DC-DC converters
- Load Switch
- SMPS





Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	100	V	
Gate-Source Voltage		V _G S	±20	V	
Continuous Drain Current	T _C = 25°C		72		
	T _C = 100°C	Ι _D	51	Α	
	T _A = 25°C]	12		
Pulsed Drain Current (Note 1)		I _{DM}	288	А	
Single Pulse Avalanche Current (N	ote 2)	las	14.9	А	
Single Pulse Avalanche Energy (Note 2)		Eas	33.3	mJ	
Total Power Dissipation	T _C = 25°C	Б	115	W	
	T _C = 125°C	P _D	38		
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +175	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	Rejc	1.3	°C/W	
Junction to Ambient Thermal Resistance (Note 3)	R _{OJA}	50	°C/W	

1

Notes:

- 1. Pulse Width ≤ 100µs.
- 2. L = 0.3mH, V_{GS} = 10V, R_{G} = 25 Ω , Starting T_{J} = 25 $^{\circ}$ C.
- 3. Device on a PCB FR4 with 1 in² (single layer, 2 oz thickness) copper area for drain connection.



PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 1mA$	BV _{DSS}	100			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V _{GS(TH)}	2.4	2.9	3.6	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
	V _{GS} = 0V, V _{DS} = 100V	I _{DSS}			1	μA
Drain-Source Leakage Current	V _{GS} = 0V, V _{DS} = 100V T _J = 125°C				100	
Drain-Source On-State Resistance	V _{GS} = 10V, I _D = 36A	_		8.2	10	mΩ
(Note 4)	V _{GS} = 7V, I _D = 36A	R _{DS(on)}		9.2	12	
Forward Transconductance (Note 4)	$V_{DS} = 10V, I_{D} = 9A$	g fs		33		S
Dynamic (Note 5)						
Total Gate Charge	V _{DS} = 50V, I _D = 12A, V _{GS} = 7V	Qg		14		nC
Total Gate Charge	V _{DS} = 50V, I _D = 12A, V _{GS} = 10V	Qg		20		
Gate-Source Charge		Q _{gs}		5.9		nC
Gate-Drain Charge		Q _{gd}		3.7		
Input Capacitance	V _{DS} = 60V, V _{GS} = 0V,	Ciss		1205		
Output Capacitance		Coss		226		pF
Reverse Transfer Capacitance	f = 1.0MHz	Crss		26		
Gate Resistance	f = 1.0MHz	Rg		0.5		Ω
Switching (Note 6)						
Turn-On Delay Time		t _{d(on)}	-	10		
Turn-On Rise Time	$V_{DD} = 50V, R_G = 6\Omega,$ $I_D = 12A, V_{GS} = 10V$	tr	I	27		
Turn-Off Delay Time		t _{d(off)}		18		ns
Turn-Off Fall Time		t _f	-	26		
Source-Drain Diode						
Forward Voltage (Note 4)	I _S = 36A, V _{GS} = 0V	V _{SD}			1.1	V
Reverse Recovery Time	Is = 12A,	t _{rr}		64		ns
Reverse Recovery Charge	di/dt = 100A/µs	Qrr		100		nC

Notes:

- 4. Pulse test: Pulse Width \leq 300µs, duty cycle \leq 2%.
- 5. Defined by design. Not subject to production test.
- 6. Switching time is essentially independent of operating temperature.

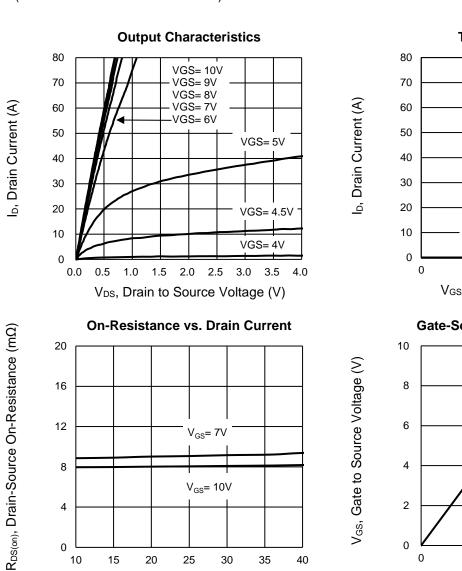
ORDERING INFORMATION

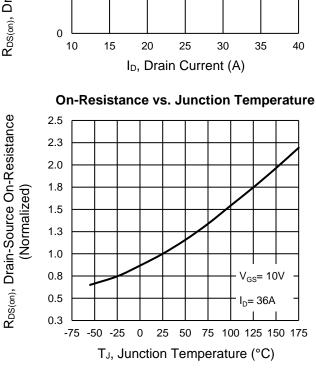
ORDERING CODE	PACKAGE	PACKING
TSM100NH10CR RLG	PDFN56U	2,500pcs / 13" Reel

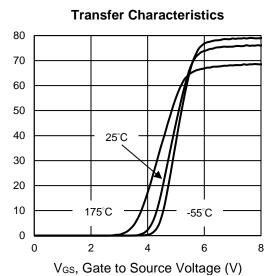


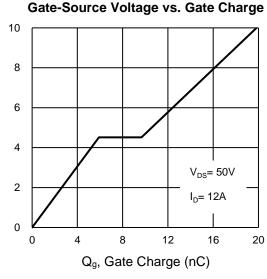
CHARACTERISTICS CURVES

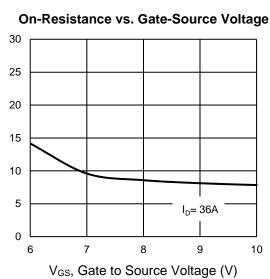
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$











 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$, Drain-Source On-Resistance (m Ω)

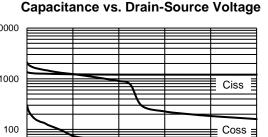
3

 $I_D = 1mA$



CHARACTERISTICS CURVES

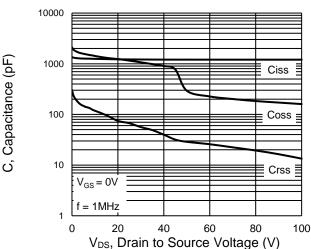
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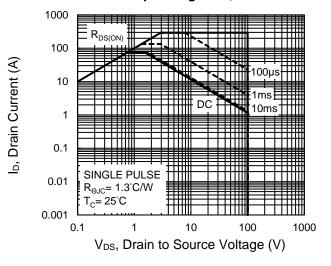
1.20 1.15 1.10 1.05 1.00 0.95 0.90

BV_{DSS} vs. Junction Temperature

-50 -25 0 25 50 75 100 125 150 175 T_J, Junction Temperature (°C)

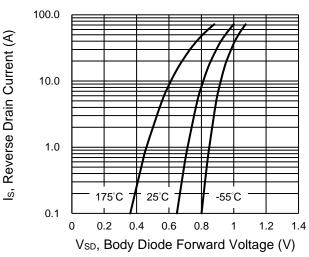


Maximum Safe Operating Area, Junction-to-Case



Normalized Effective Transient Thermal Impedance, Zeuc

Source-Drain Diode Forward Current vs. Voltage



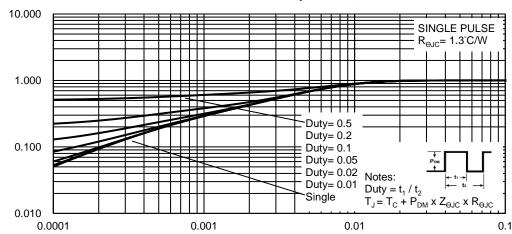
Normalized Thermal Transient Impedance, Junction-to-Case

Drain-Source Breakdown Voltage

0.85

0.80

BV_{DSS} (Normalized)



t, Square Wave Pulse Duration (sec)



Ip-Drain Current (A)

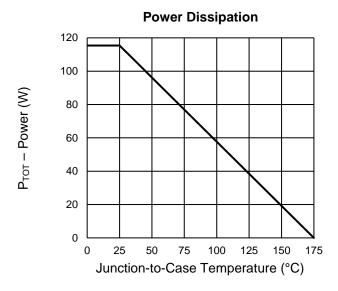
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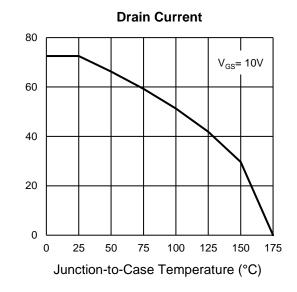


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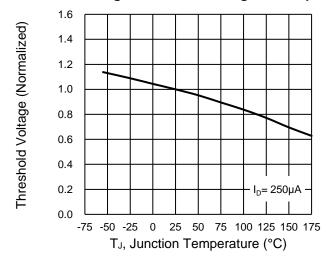
CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$





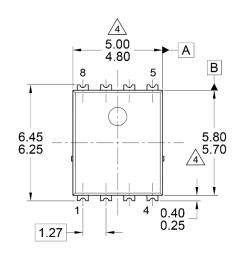
Normalized gate threshold voltage vs Temperature

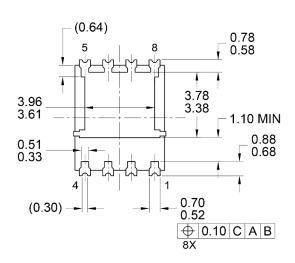


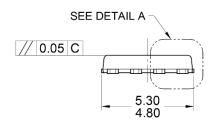


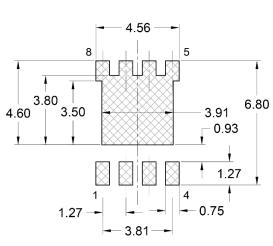
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

PDFN56U



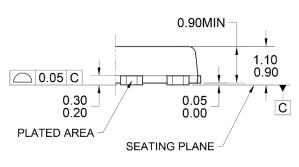




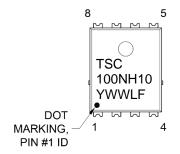


SUGGESTED PAD LAYOUT

(REFERENCE ONLY)



DETAIL A (SCALE 2:1)



MARKING DIAGRAM

NOTES: UNLESS OTHERWISE SPECIFIED

- 1. ALL DIMENSIONS ARE IN MILLIMETERS.
- 2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- 3. PACKAGE OUTLINE REFERENCE: JEITA ED-7500B, EIAJ SC-111BB.
- MOLDED PLASTIC BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- 5. DWG NO. REF: HQ2SD07-PDFN56U-023 REV B.

100NH10 = Device marking

Y = Year code

WW = Week code (01~52)
L = Lot code (1~9,A~Z)
F = Factory code



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